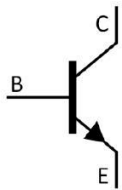


Rev.F Mar.-2016

WR0459 ММ Ё QSQ æ Ć ħ s ll 1 Silicon NPN transistor in a TO-126 Plastic Package.

лъ EG56; Ы ´
 Complementary pair with BD238.

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 Medium power linear and switching applications.

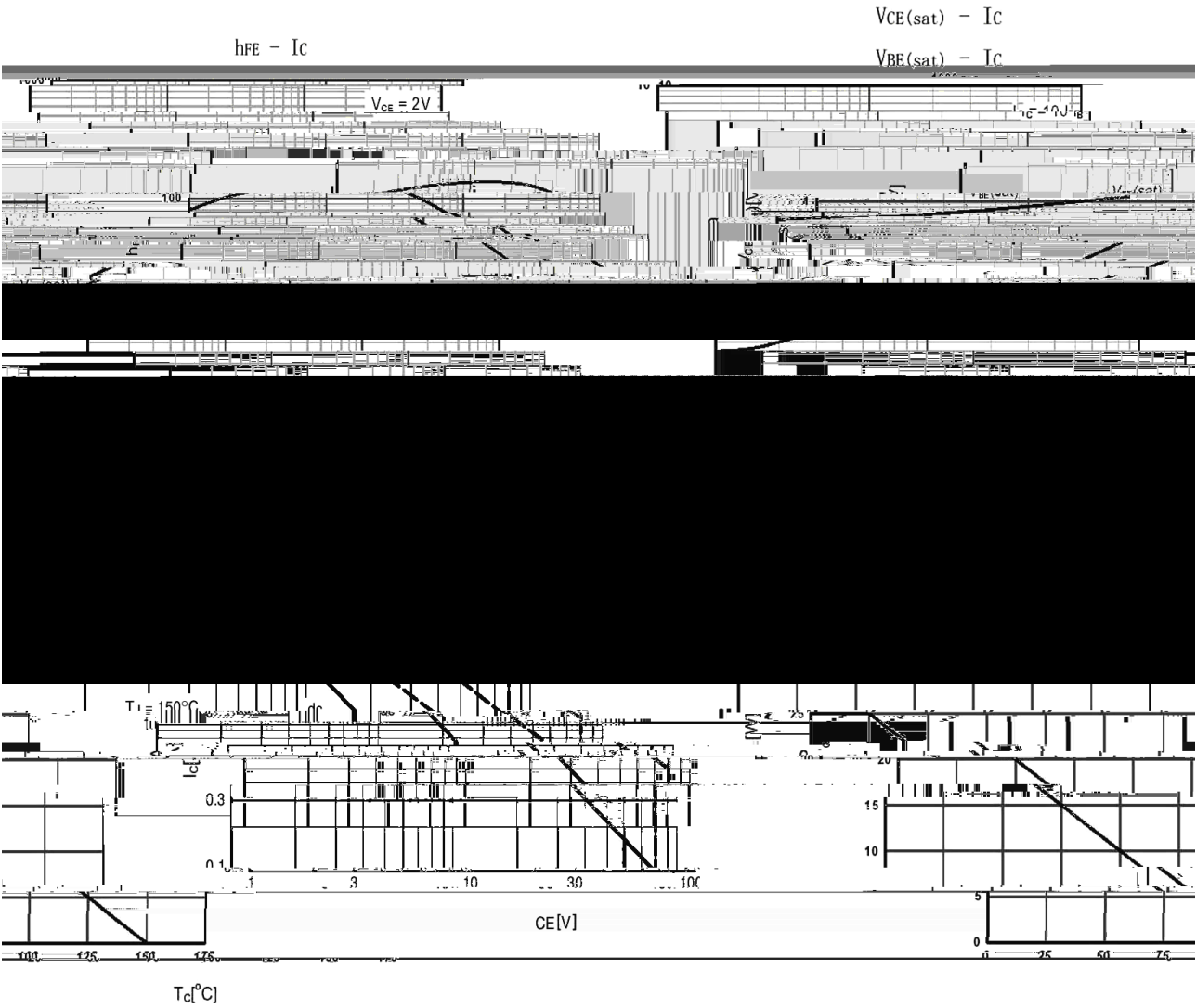


PIN1 χ Emitter PIN 2 χ Collector PIN 3 χ Base

ø m ħ ħ " See Marking Instructions.

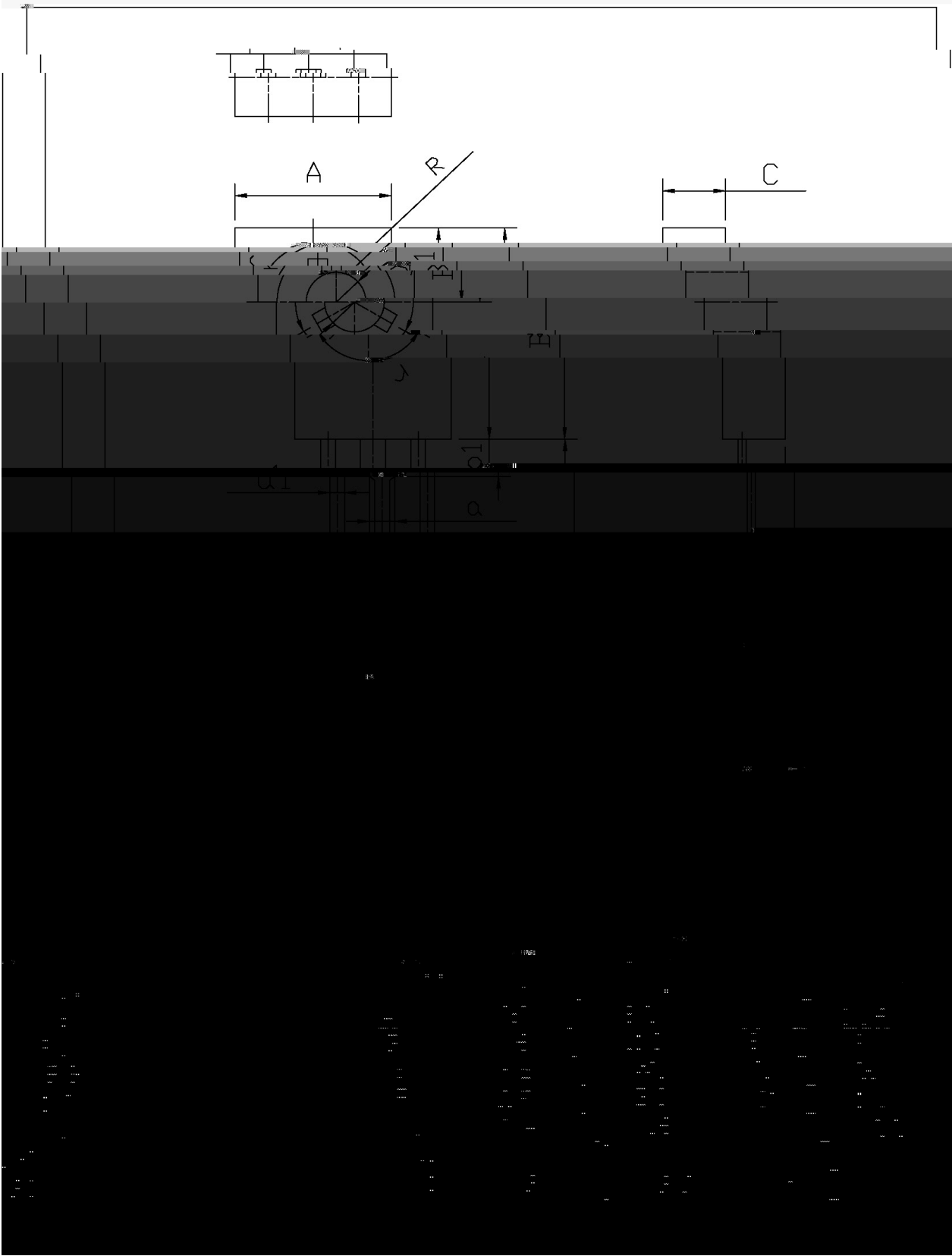
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	100	V
Collector to Emitter Voltage	V_{CEO}	80	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	2.0	A
Peak Collector Current	I_{CM}	6.0	A
Collector Power Dissipation	$P_C(T_C=25^\circ C)$	25	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

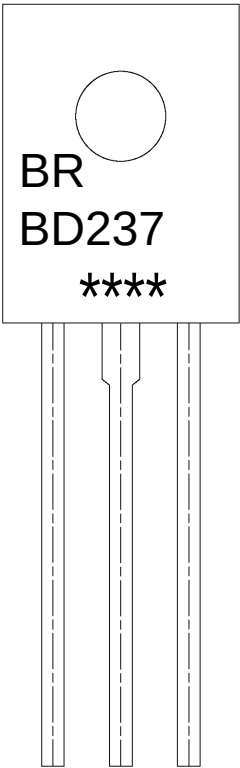
Parameter	Symbol	Test Conditions	Min	Max	Unit
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T□-126

单位: mm





公司代码	公司代码
EU	公司代码
EG56:	公司代码
----	公司代码
Note:	
BR:	Company Code
BD237:	Product Type.
****:	Lot No. Code, code change with Lot No.

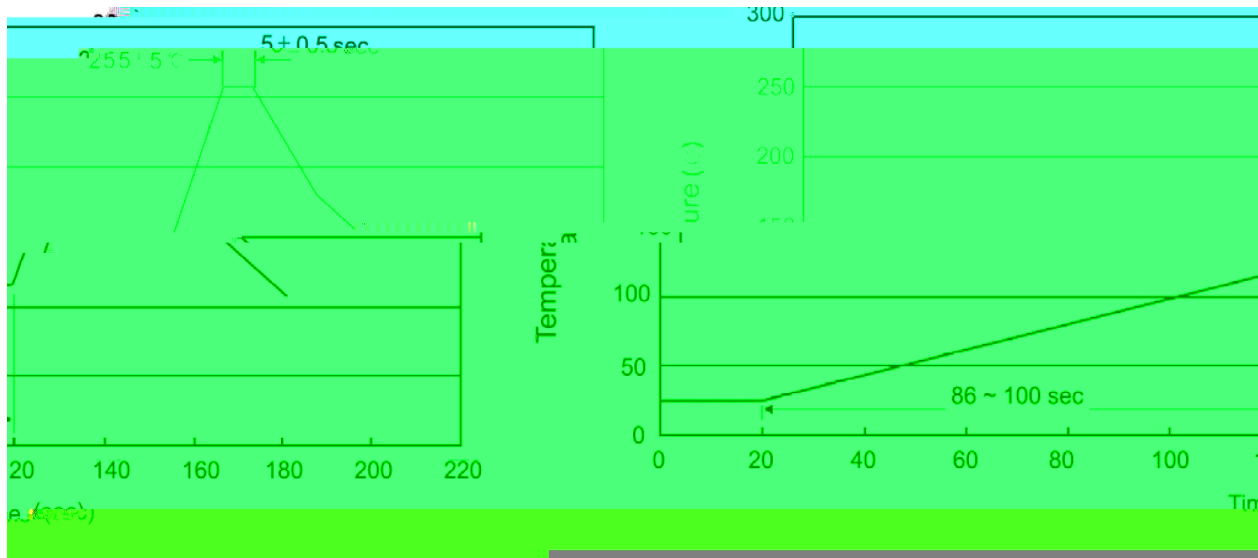


图 3

Note: